



AF ^{LV}

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

RALF VAN BENTUM

MANFRED HORSTMANN

Examiner: Lan Vinh

OK to enter

Group Art Unit: 1765

LV

Serial No.: 10/624,712

Att'y Docket: 2000.106700/DE0122

2/14/06

Filed: July 22, 2003

Customer No.: 23720

For: TECHNIQUE FOR FORMING
CONTACTS FOR BURIED DOPED
REGIONS IN A SEMICONDUCTOR
DEVICE

RESPONSE TO FINAL OFFICE ACTION DATED JANUARY 6, 2006

Mail Stop AF

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

CERTIFICATE OF MAILING
37 C.F.R. 1.8

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on the date below:

January 26, 2006

Date

Mary Paul
Signature

Sir:

This paper is submitted in response to the Final Office Action dated January 6, 2006, for which the three-month date for response is April 6, 2006.

No fees are believed to be due in connection with the present paper. However, should any fees be required under 37 C.F.R. §§ 1.16 to 1.21, the Director is authorized to deduct such fees from the Advanced Micro Devices, Inc. Deposit Account No. 01-0365/DE0122.¹

Reconsideration of the application in view of the following amendments and remarks is respectfully requested.

¹ In the event the monies in that account are insufficient, the Director is authorized to withdraw funds from Williams, Morgan & Amerson, P.C. Deposit Account No. 50-0786/2000.106700.